

Resistive Electrodes

G. Morello on behalf of WG3

DRD1 Meeting, January 31st 2024

Resistivity

The resistive electrodes were introduced in particle detectors with the aim to localize the reduction of the electric field due to a discharge occurrence $\lceil \Omega m \rceil$

Several technologies for particle detectors are nowadays based on resistive electrodes.

It is worth distinguish between **bulk resistivity (Ωm)** and **surface resistivity (Ω/□)** when H<<W,L

Resistive Plate Counter

FEW EXAMPLES of resistive materials used in RPCs

Source: M. Abbrescia, V. Peskov, P. Fonte, Resistive Gaseous Detectors, Wiley-VCH, 2018

Other alternative materials under study are lower resistive glasses, ceramics, plastic with resistivity around 1E10 Ω cm (see Wang Yi and Giulio Aielli talks)

Semi-conductors (ex. GaAs) are good candidates as the resistivity is lower (1.4E8 Ωcm) \rightarrow G. Aielli's talk

Resistive Plate Counter

Figure 3. RPC efficiency as function of the field strength for three RPC detectors performed with two readout systems: squares — MAXIM3760+CAEN TDC, triangles — PADI-10. The corresponding bulk resistivities of the ceramic plates on floating potential are given in the legend.

Fig. 3. Dependence of the bulk resistivity of phosphate glass on high voltage.

10.1088/1748-0221/15/12/C12004

Figure 7. Measured counting rate for three different value of the absorption factor as a function of the high voltage.

Further interesting developments in HTTP://CDS.CERN.CH/ RECORD/2319919

Resistive MPGDs

ATLAS MicroMegas were the firstg MPGD introducing a resistive stage by screen printing (O(1MΩ/□)), example recently followed for RETGEM detectors.

Other MPGDs start exploiting the properties of Diamond-Like Carbon (DLC), an amorphous layer of graphite, already extensively used in industry for its mechanical properties. In our case we care the electrical properties. Needing different values of surface resistivity: around 10 MΩ/ \Box for the MM and around 100 MΩ/ \Box for the u-RWELL The segmentation of the resistive layerand/or a more dense grounding network brings to largerrate capability

Micro-Pattern Gaseous Detectors

https://cds.cern.ch/record/1395690/files/EPS-HEP2011_406.pdf https://iopscience.iop.org/article/10.1088/1748-0221/10/02/P02008/pdf

Surface Resistive Plate Counter

DLC-based RPC:

- **From bulk resistivity to surface resistivity**: easy tunable resistivity w.r.t. bakeliteor glass
- μ-RWELL inspired**High Rate schemes**
- Flexible substrate

A promising novel technology, from MPGD material and technology experience.

https://arxiv.org/pdf/2401.13553.pdf

Figure 13: Time difference between the RPC and the trigger counter in the highrate measurement. The peak comes from detected positrons and the baseline comes from accidental muon hits.

M. Giovannetti, RD51 Coll. Meeting, June 2023

My personal view…

The magnetron sputtering machine

- The field creates ion-electron pairs in the plasma
- The electrons area accelerated and furtherly ionize the plasma generating new ions
- A magnetic field concentrate the ions in a peculiarregion of the targer(speed track)
- The ions drift towards the target and by collision the material is extractedflying all over the vacuum chamber

Machine co-funded by CERN and INFN. R&D led by INFN LNF, Roma3 and Na

The graphite target The three external cathodes

DLC tests: modus operandi

SAMPLES

- APICAL foil dried in the oven (at least 16h at 100 °C)
- Three rectangular samples, 15×10 cm2 (machine operating in oscillation mode), to check the uniformity of the deposition along z
- A small 1.5 x 1.5 cm2 glass next to each sample for thickness measurement

RUN

- Pure Ar -based plasma surface treatment (plasma etching)
- Pure Ar-based pre-sputtering process
- Sputtering process

POST RUN

- Resistivity measurements
- Baking of one sample from each run (2h at 220 °C) to simulate the thermal shock during detector manufacturing
- Monitoring of the resistivity during the following days (stability check)

Repetitivity and stability with N2

First testswith N2 answeredto two urgent questions:

- 1) Standing the same deposition parameters, will the resisitivitybe the same or will it change?
- 2) How does the resistivity change along the time?

Measurements in Mohm/sq. Quite satisfactory repetitioncapability Further confirmations for other dep. conditions

Summaryof the test with C2H² (Sept. 2023)

- 1. Scans in acetylene percentage (1.5% 5%) at p_proc = 2.E-3 mbar, t_dep = 15 m and P_cat = 1 kW
- 2. Scans in acetylene percentage (4% 8%) at p_proc = 2.E-3 mbar, t_dep = 15 m and P_cat = 2 kW
- 3. Test at different deposition time (15 m 240 m) with 4% of C2H2 at p_proc 8.E-3 and P_cat = 1 kW
- 4. Repetitivity tests (C2H2 3%, p_proc = 2.E-3, P_cat = 1kW, t_dep = 22.5 m)
- 5. Uniformity tests

Stability with C2H² (Sept. - Oct. 2023)

A drop after the baking and a small drift, but then very stable values

Deposition time and repetitivity test

 \circ

 0.5

0

 $\overline{\circ}$ $\overline{\circ}$ $\overline{\circ}$ $\overline{\circ}$ $\overline{\circ}$

20

40

50

60 z (cm)

10

From now on, we use a single APICAL sample 60 x 10 cm2 We measure the resistivity along the longitudinal axis

Summaryof the test with C2H² (Nov. 2023)

mask The mask seems promising. The uniformity region has been extended to about 45 cm. Further improvements con be achieved with a different mask shape

- The community shows a huge interestin resistive materials, since they can improve the stabilityof the detectors
- In RPCs field new lower bulk resistive materials have been introduced to improve the rate capability keeping the other features unchanged
- A link from bulk resistive material borrowed by MPGDs with the birth of RPWELL
- The DLC createdanother strong link between the MPGD technologies and the RPC world with the introduction of the sRPC technology
- The presence of the CID machine at CERN should provide a remarkable production of this resistive materialfor the early mentioned applications
- The tests done so far are very promising
- The production is likely to start in 2024

Spare

Micro-Pattern Gaseous Detectors

MHz/cm² (to be scaled by three for mip) is **extrapolated.**

The flux is limited by the capability of the X-ray gun

DLC tests

The machine phase-space is quite huge; the plan for the tests have been focused to few parameters.

QUICK GLOSSARY

Pressure limit: *the pressure of the vacuum at which the run starts. Typically 2.E-5 mbar*

Pressure process: *the pressure of the plasma during the sputteringphase* **Power:** *the maximum power limit output from the DC PS on the cathode* **Time deposition:** *the duration of the sputtering process*

- Ar-N₂ plasma tests
	- Scan in nitrogenpercentage at a given pressure process
	- Scan in pressure process at a given nitrogen percentage
	- Tests with different time deposition
- Ar-C₂H₂ plasma tests
	- Scan in acetylene percentage at a given pressure process and power
	- Scan in time deposition at a given pressure process, acetylene percentage and power
	- Uniformity tests

Tests in pure Argon

Summaryof the test with N² (June 2023)

Nevertheless these tests have been helpful to understand the dependance of the resisivity on the quantity of the second component of the plasma and on the pressure process

Very large amount of nitrogen to reach the target resistivity (50 – 200 Mohm/sq.)

Uniformity test

C2H2 4%, 2.E-3 mbar, time = 15 min, $P = 1$ kW C2H2 5%, 2.E-3 mbar, time = 10 min, $P = 2$ kW ρ (G Ω /sq.) 2.5 ρ (G Ω /sq.) \circ 1.4 Pre-baking Pre-baking \circ \circ ۱o Post-baking ۰ Post-baking ۰ ۰ \circ 1.5 \circ ô 0.8 O \circ \circ 0.6 С O \bullet \circ \circ \circ \circ \circ C \circ 0.4 0.5 ™o™omor O $\overline{\circ}$ $\overline{\circ}$ $\overline{\circ}$ 0.2 30 40 50 20 30 50 60 Ω 10 20 Ω 10 40 z (cm) z (cm)

The baking, as expected, doesn't change the thickness profile These tests pointed out that the deposition, along the axis, is uniform in a very narrow central region We would like to have a uniformity $\leq 15\%$ **THIS REGION MUST BE EXTENDED**

Summaryof the test with C2H² (Nov. 2023)

To improve the uniformity, Serge's idea is to install a mask stuck to the shutter to reduce the material extractionin the central part of the target

Lower extraction \rightarrow thinner deposition \rightarrow larger resistivity

